

REMARKS

The specification has been amended to correct the description of Figure 9 in the Brief Description of the Drawings.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

FIG. 9A and FIG. 9B [FIG. 9A to FIG 9C] are cross-sectional views illustrating some steps in the method for manufacturing a semiconductor device according to the fourth embodiment, from the removal of an unreacted second cobalt film up to the formation of a fourth silicide film.

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